

# **isc Silicon NPN Darlington Power Transistor**

2SD1988

### **DESCRIPTION**

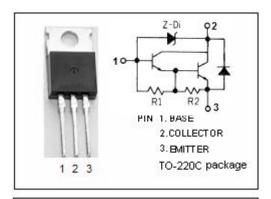
- · High DC Current Gain-
  - :  $h_{FE} = 3000(Min)@I_{C} = 1A$
- · Low Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)} = 1.5V(Max)@ I_{C} = 1A$
- Incorporating a built-in zener diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

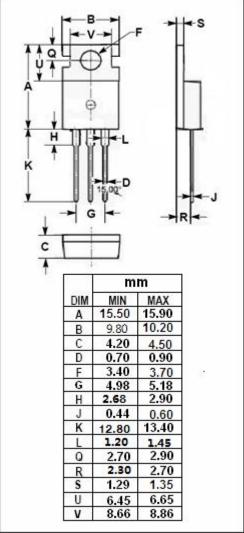


- · Low-frequency amplifications.
- · Power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	40-50	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	40-50	V	
$V_{EBO}$	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	2	А	
I <sub>CM</sub>	Base Current-Peak	3	А	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25℃	25	W	
Тл	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	40		50	V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =0.1mA; I <sub>E</sub> = 0	40		50	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 1mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 1mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>E</sub> = 0			10	μ <b> A</b>
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	3000			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 100mA; V <sub>CE</sub> = 5V		100		MHz

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